

IN THE SPECIFICATION

Please amend the paragraph of page 11, line 16 to line 19 with the following:

In the present invention, the dielectric layer 230, which can be, for example, an ATA layer, is preferably formed in-situ. Thus, it is preferable to use a clustered apparatus including a chamber for forming the ~~AlO~~ AlO layer and a chamber for forming a high *k*-dielectric layer such as TaO layer in order to support the in-situ process.